

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S5	1	("6153520").PN.	USPAT; USOCR	OR	OFF	2004/10/25 10:43
S9	1	("6524939").PN.	USPAT; USOCR	OR	OFF	2005/09/22 14:22
S12	7	(("6291839") or ("6078064") or ("5804839") or ("6008539") or ("6335218") or ("6258618") or ("5438006")).PN.	USPAT; USOCR	OR	OFF	2007/02/13 10:34
S13	1	"5656832".PN.	USPAT	OR	ON	2004/10/21 14:56
S15	0	(438/671.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S16	0	("438"/\$.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S17	0	("257"/\$.ccls. with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:07
S18	197	(438/671).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 07:07
S19	0	((438/671.ccls.) with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:08
S20	8999	(semiconductor with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:38

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S21	24	(semiconductor with (dry adj etch\$5) with (light adj emitting adj device)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:40
S22	15	(semiconductor with (dry adj etch\$5) with (light adj emitting adj device)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:49
S23	3	(semiconductor with metal with (dry adj etch\$5) with (light adj emitting adj device)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 07:10
S24	134	((semiconductor) with ((silicon or ("S")) adj (layer or film))) and ((metal adj (film or layer)) with (dry adj etch\$5))) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/22 13:40
S25	1	("6777294").PN.	USPAT; USOCR	OR	OFF	2005/09/22 14:33
S26	1	("6790718").PN.	USPAT; USOCR	OR	OFF	2007/02/07 16:09
S27	1	("20040185599").PN.	US-PGPUB	OR	OFF	2006/03/27 13:40
S28	3764	(semiconductor with (dry adj etch\$5)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:49
S29	173	(semiconductor near (dry adj etch\$5)) and metal and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:49
S30	60	(semiconductor near (dry adj etch\$5)) and (metal adj (layer or film)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:48

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S31	0	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) near (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:50
S32	6	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) with (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:51
S33	15	(semiconductor adj body) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:56
S34	373	(interconnect\$4) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 14:56
S35	365	semiconductor and (interconnect\$4) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:20
S36	15	semiconductor and (interconnect\$3) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) same (dry adj etch\$5)) and @ad<="20010927" and (platinum and palladium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:22
S37	137	semiconductor and (interconnect\$3) and (nitride adj (layer or film or compound)) and ((metal adj (layer or film)) and (dry adj etch\$5)) and @ad<="20010927" and (platinum and palladium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/07 15:22
S38	16	substrate and ((nitride adj compound adj semiconductor) adj (layer or film)) and (metal adj (layer or film)) and (dry adj etch\$4) and partial\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/30 13:29
S39	1	("5838029").PN.	USPAT; USOCR	OR	OFF	2007/02/08 14:42

## EAST Search History

S42	3	("6562465").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/08 14:42
S43	12	(("5838029") or ("5814533") or ("7096873") or ("7071015") or ("6969873") or ("6858866") or ("6735230") or ("6680492") or ("6657237") or ("6376866") or ("6087681") or ("6083841")).PN.	USPAT; USOCR	OR	OFF	2007/02/13 10:54
S44	2	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) with ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:16
S45	9	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:15
S46	0	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) near ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 11:15
S47	8	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj etch\$4) and ((mask\$4 or photo or photoresist or resist) same ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14

## EAST Search History

S48	0	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) same ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14
S49	0	("5838029" "5814533" "7096873" "7071015" "6969873" "6858866" "6735230" "6680492" "6657237" "6376866" "6087681" "6083841"). pn. and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub.2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:14
S50	0	(nitride adj compoung adj semiconductor) and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub. 2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:15
S51	1	(nitride adj compound adj semiconductor) and (dry adj chemical\$2) and ((mask\$4 or photo or photoresist or resist) and ((silicon adj oxide) or ("SiO.sub. 2")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/13 12:15